

FIG. 1

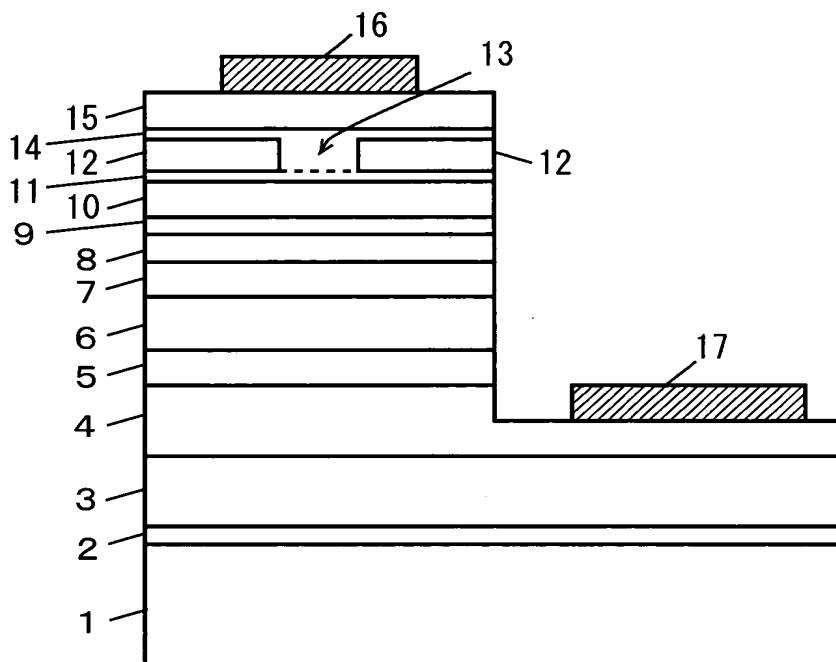
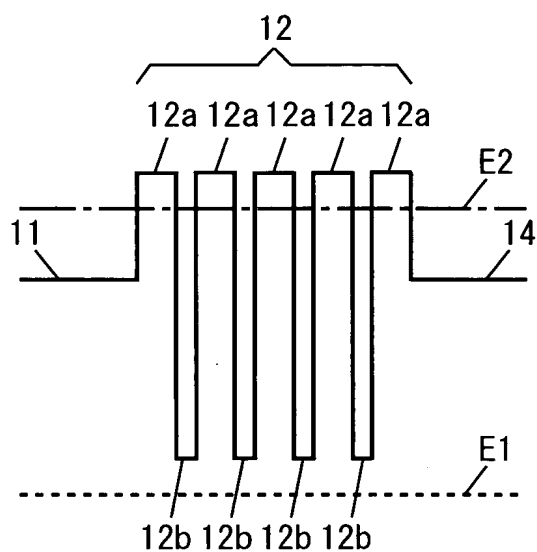


FIG. 2



1.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = \int_{\mathbb{R}^n} u \Delta u dx$   
 2.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = - \int_{\mathbb{R}^n} |\nabla u|^2 dx$   
 3.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = \int_{\mathbb{R}^n} u \Delta u dx$   
 4.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = - \int_{\mathbb{R}^n} |\nabla u|^2 dx$   
 5.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = \int_{\mathbb{R}^n} u \Delta u dx$   
 6.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = - \int_{\mathbb{R}^n} |\nabla u|^2 dx$   
 7.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = \int_{\mathbb{R}^n} u \Delta u dx$   
 8.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = - \int_{\mathbb{R}^n} |\nabla u|^2 dx$   
 9.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = \int_{\mathbb{R}^n} u \Delta u dx$   
 10.  $\frac{1}{2} \frac{d}{dt} \int_{\mathbb{R}^n} |u|^2 dx = - \int_{\mathbb{R}^n} |\nabla u|^2 dx$

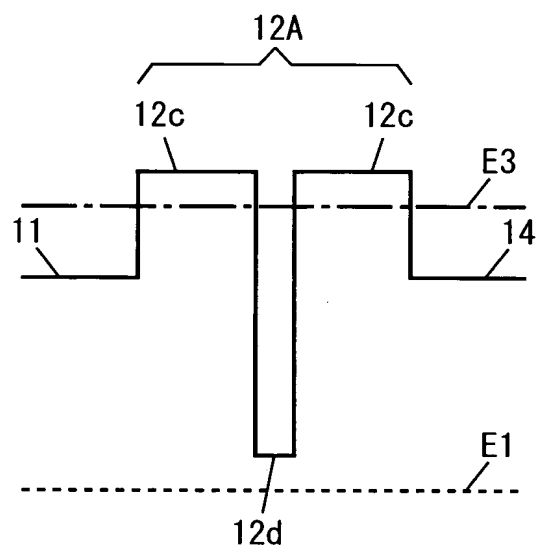
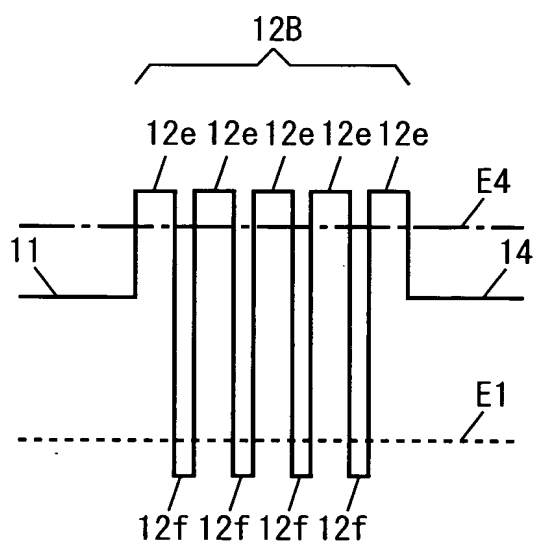
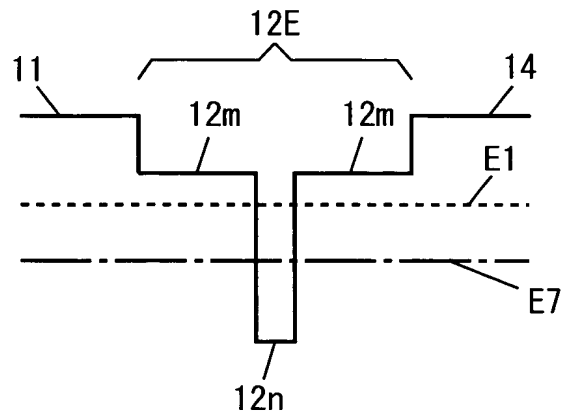


FIG. 4



A cross-sectional view of a semiconductor device. A gate stack 12D is formed on a substrate 11. The gate stack 12D consists of alternating layers 12i and 12k. A top layer 14 is formed on the substrate 11. A dashed line E1 is shown below the gate stack 12D, and a solid line E6 is shown below the substrate 11.

F I G. 7



F I G. 8

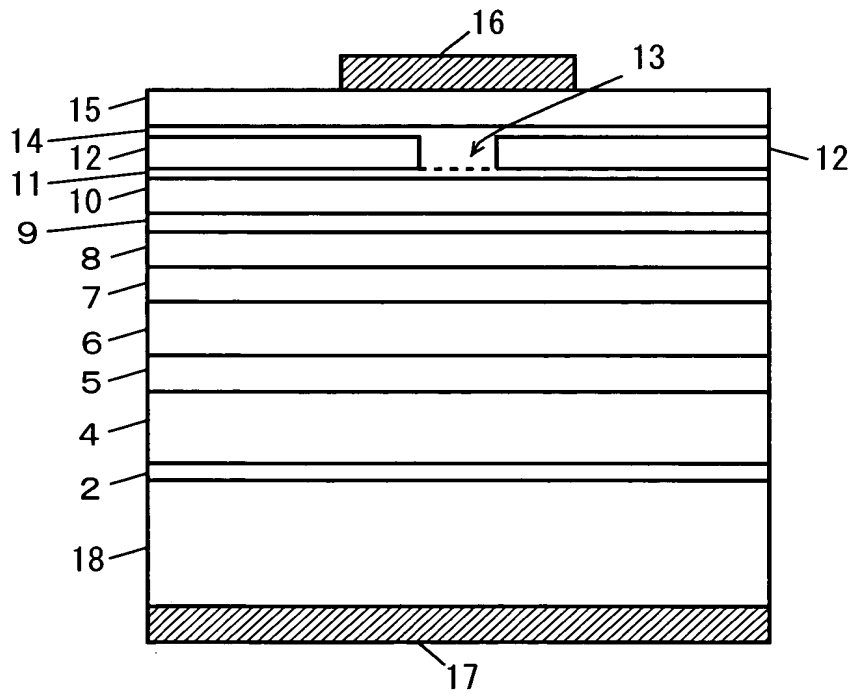


FIG. 9

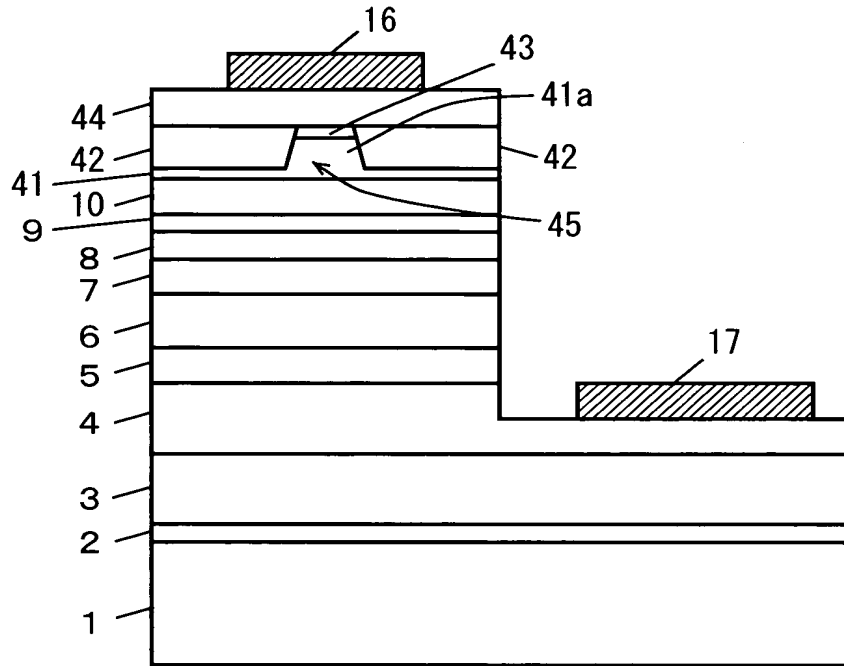
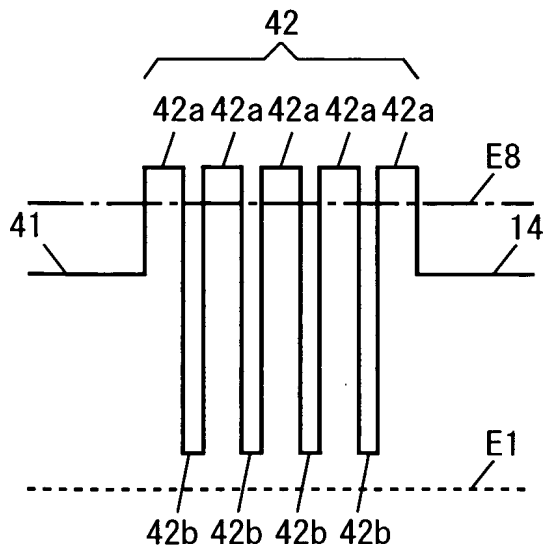


FIG. 10



002250" E / 3660

FIG. 11

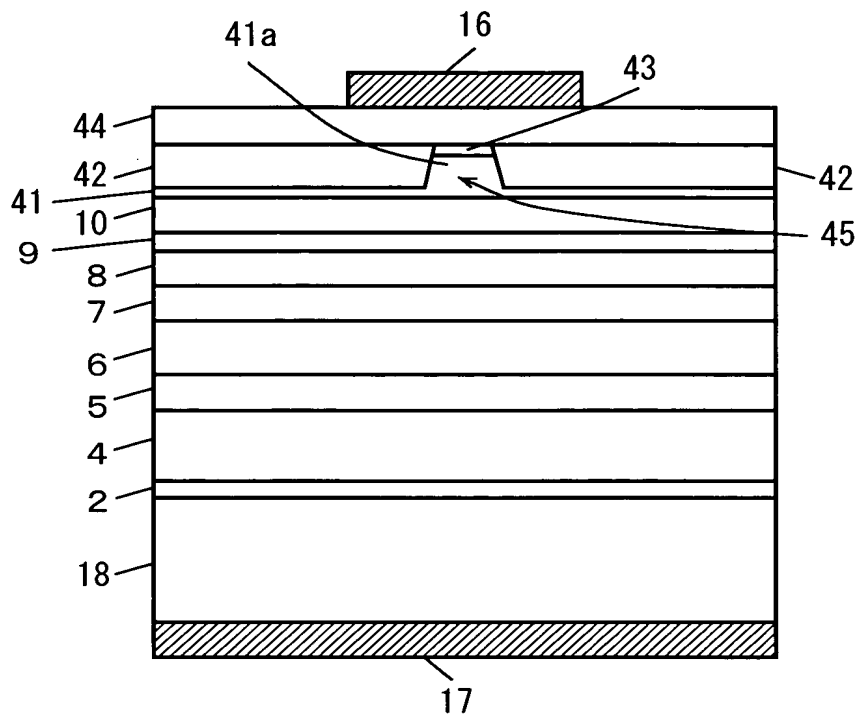


FIG. 12 PRIOR ART

